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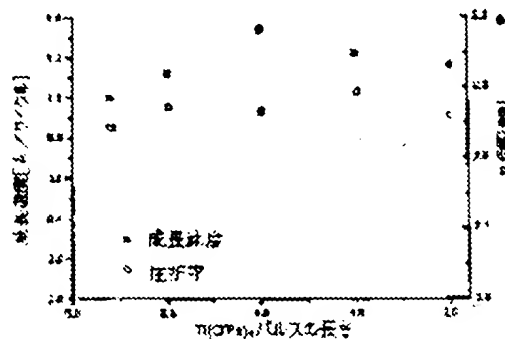
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(54) METHOD OF GROWING OXIDE THIN FILM

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a method of growing an oxide thin film on a substrate.

SOLUTION: In the method of growing an oxide thin film according to the principle of the ALD method where an oxide thin film is deposited onto a substrate by an alternating surface reaction of metallic raw material and oxygen raw material, the oxygen raw material to be used is composed of a compound of boron, silicon or metal having at least one organic ligand, and the oxygen is combines with at least one atom of boron, silicon or metal.



LEGAL STATUS

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